



CASE SE/2-22853/A/PCT

**CERTIFICATE OF MAILING**

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to the: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**IN RE APPLICATION OF**

**PATRICE BUJARD ET AL**

**APPLICATION NO: 10/517,283**

**FILED: DECEMBER 8, 2004**

**FOR: PLANE-PARALLEL STRUCTURES OF  
SILICON/SILICON OXIDE**

**Group Art Unit: 1755**

**Examiner: HAILEY, PATRICIA L.**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

**DECLARATION UNDER RULE 132**

Patrice Bujard, the undersigned, states:

That I received a Ph. D. in Physics from University of Geneva;

That I have been employed by Ciba Specialty Chemicals Corporation since 1985;

That I have approximately 20 years of chemical research and development experience; that from January 1985 to date I have worked in the Research and Development laboratories of Ciba Specialty Chemicals Corporation;

That I invented the subject matter disclosed but not claimed in U.S. Pub. Pat. Appl. No. 2005/0161678 related to plane parallel structures of  $\text{SiO}_y$  wherein  $1 \leq y \leq 1.8$ ,  $\text{SiO}_2$  flakes having "a high plane-parallelism" and various uses thereof, in particular the material of paragraphs 75, 126 and 147-162 of the US Published application relied on by the Examiner for rejections of claims 1-6, 9-11 and 13-18.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under 18 U.S.C. § 1001, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.



Patrice Bujard